

# ACKNOWLEDGEMENT RECEIPT

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## Title of Invention

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE LAYER  
AND TUNNEL OXIDE LAYER IN AN EEPROM CELL

Submission Type : Information Disclosure  
Statement

Application Number:

10/717149



EFS ID:

88332

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First Named Applicant: Alan Renninger

Attorney Docket Number: ATM-262

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File Listing:

Doc. Name	File Name	Size (Bytes)	Date Produced (yyyymmdd)
us-ids	Atm262-usidst.xml	1765	2005-07-18
us-ids	us-ids.dtd	7763	2005-07-18
us-ids	us-ids.xsl	12026	2005-07-18
package-data	Atm262-pkda.xml	1759	2005-07-18
package-data	package-data.dtd	27025	2005-07-18
package-data	us-package-data.xsl	19263	2005-07-18
Total files size		69601	

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